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WHAT IS CLAIMED IS:

1. A process for welding a Ti material and a Cu material comprising: interposing a welding Cu material, including a tertiary metal as a component, between a Ti material and a Cu material;

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said tertiary material being of a type which performs one of the following:

reduces a three-element eutectic temperature of the Ti, the
Cu and said tertiary metal below a eutectic temperature of said Ti
and the Cu; and

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produces a reaction which causes a liquid phase at a

temperature that is lower than a two-element eutectic temperature

between the Ti material and the Cu material;

heating said Ti material and the Cu material to said temperature wherein solid and liquid coexist; and

maintaining said temperature long enough to form a welding portion.

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- 2. A welding process of a Ti material and a Cu material according to claim 1, wherein the step of heating includes heating in a non-oxidizing atmosphere of one of a vacuum, an inert gas, and a reducing gas.
- 3. A welding process of a Ti material and a Cu material according to claim 1 wherein said tertiary metal is Sn.
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- 4. A welding process of a Ti material and a Cu material according to claim 3, where said temperature is from about 700° C to about 887° C.

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- 5. A welding process of a Ti material and a Cu material according to claim 4, wherein a welding portion formed has Cu as a main body.
- 6. A welding process of a Ti material and a Cu material according to claim 5, wherein a welding portion formed includes at least 60 weight % Cu.
- 7. A welding process of a Ti material and a Cu material according to claim 1, wherein said welding Cu material is a foil or a powder.
- 8. A welding process of a Ti material and a Cu material according to claim 1, wherein the welding Cu material is composed of plating of said tertiary metal on a Cu foil.
- 9. A Ti-Cu composite plate having a welding portion formed by the process of claim 1.

10. A sputtering target backing plate wherein a Ti-Cu composite plate of the claim 9 is used to bond the target member on the side of the Cu material.

- 11. A sputtering target backing plate, wherein said welding Cu material includes a foil Cu material having thereon at least one of a coating and a powder of said tertiary metal to improve wettability of said Ti material.
- 12. A sputtering target backing plated according to claim 11, wherein said teritary metal is Sn.

13. A process for forming a plate including:

interposing a tertiary metal between a Cu material and a Ti material; said tertiary metal being of a type which reacts with at least one of Cu and Ti to reduce a melting temperature below a temperature of an eutectic temperature of said Cu and Ti material; and

holding said materials at said temperature for a time sufficient to obtain welding.

- 14. A welding process of a Ti material and a Cu material according to claim 6, wherein said welding Cu material is a foil or a powder.
- 15. A welding process of a Ti material and a Cu material according to claim 6, wherein the welding Cu material is composed of plating of said tertiary metal on a Cu foil.

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